

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S71	135647	(sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 11:05
S73	10	S71 near15 (ingot or boule) same pattern\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 11:06
S72	398	S71 near15 (ingot or boule)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 11:06
S70	2	"20020170491".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 11:08
S74	2	"20040144299".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 11:31
S75	2	"5853478".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 14:32
S76	666	pattern\$5 and single near2 crystal\$5 near5 (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 14:33
S77	21	seed\$5 near10 pattern\$5 and single near2 crystal\$5 near5 (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 14:38
S78	433	single near2 crystal\$5 near5 (sic or silicon near2 carbide) same (pvt physical near2 vapor near2 transport\$5 or sublimat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 14:42

S80	16	single near2 crystal\$5 near5 (sic or silicon near2 carbide) near10 (bulk or large or boule or ingot) same (pvt physical near2 vapor near2 transport\$5 or sublimat\$5) and lateral near2 (grow\$4 or overgrow\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 14:56
S79	25	single near2 crystal\$5 near5 (sic or silicon near2 carbide) same (pvt physical near2 vapor near2 transport\$5 or sublimat\$5) and lateral near2 (grow\$4 or overgrow\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 14:56
S81	142	single near2 crystal\$5 near5 (sic or silicon near2 carbide) near10 (bulk or large or boule or ingot) same (pvt physical near2 vapor near2 transport\$5 or sublimat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 16:12
S82	80	(sic or silicon near2 carbide) near10 (lateral near5 (grow\$4 or overgrow\$) or elo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 16:37
S85	26	(sic or silicon near2 carbide) near10 (boule or ingot) and (pvt sublimat\$4) and mask\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 16:39
S84	133	(sic or silicon near2 carbide) near10 (boule or ingot) and (pvt sublimat\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 16:39
S83	9	(sic or silicon near2 carbide) near10 (lateral near5 (grow\$4 or overgrow\$) or elo) and (boule or ingot)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 16:39
S86	8	("6056820" "5853478" "5753038" "6063185").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 15:50
S87	55	lateral near2 grow\$5 near10 (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 16:32

S90	350	S88 same seed\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 16:33
S89	419	S88 and seed\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 16:33
S88	733	(sic or silicon near2 carbide) near10 (pvt or physical near2 vapor near2 transport\$4 or sublimat\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 16:33
S91	5	S88 same seed\$5 near15 pattern\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/27 16:34
L1	82	"962963"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 13:17
S92	6	S88 same seed\$5 near15 mask\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:31
S32	108	pattern\$3 near5 (susceptor or holder) and ("117"/\$4.ccls. or "118"/\$4.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:31
S9	18	(Sic or silicon adj carbide) and (pattern\$4) same (susceptor or holder) and "117"/\$4.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:31
S5	3	(physical adj vapor adj transport or PVT) and "117"/\$4.ccls. and selectiv\$4 same (deposit\$4 or growth)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:31
S2	68	physical adj vapor adj transport or PVT and "117"/\$4.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:31

L8	110	physical adj vapor adj transport or PVT and "117"/\$4.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:31
L7	146	pattern\$3 near5 (susceptor or holder) and ("117"/\$4.ccls. or "118"/\$4.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:31
L6	587	(Sic or silicon adj carbide) and (pattern\$4) and "117"/\$4.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:31
L5	8	(physical adj vapor adj transport or PVT) and "117"/\$4.ccls. and selectiv\$4 same (deposit\$4 or growth)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:31
L4	6	L3 same seed\$5 near15 mask\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:31
L3	733	(sic or silicon near2 carbide) near10 (pvt or physical near2 vapor near2 transport\$4 or sublimat\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:31
S68	14	uchida.in. and silicon adj carbide same hexagon\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:35
L11	103	stephan near2 mueller.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:35
L10	15	stephan near2 mueller.in. and (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:35
L9	25212	stephan nar2 mueller.in. and (sic or silicon near2 carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:35